KEC

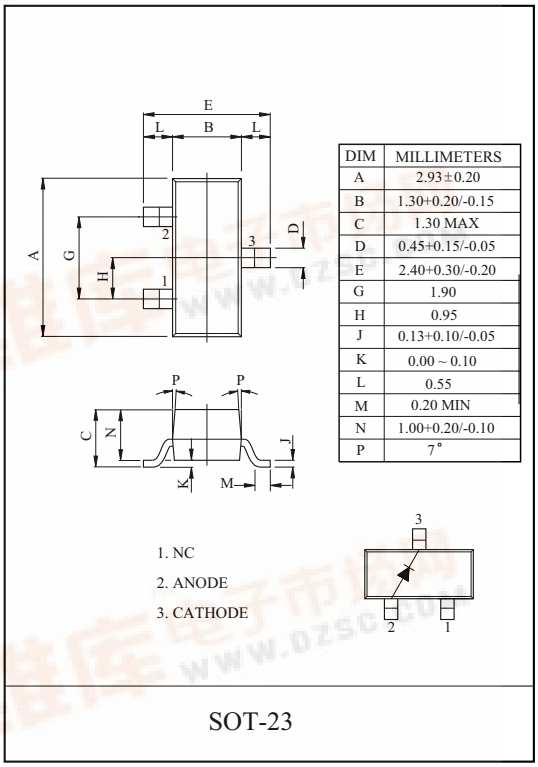
SEMICONDUCTOR
TECHNICAL DATA

KDR400S
SCHOTTKY BARRIER TYPE DIODE

High frequency rectification.
Switching power supply.

FEATURES

· Low Forward Voltage : V_F max=0.55V.
· I_O=500mA recification possible.



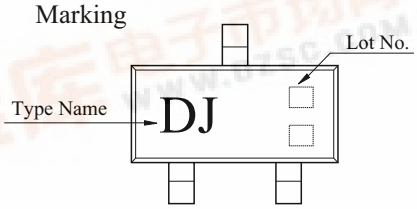
DIM	MILLIMETERS
A	2.93±0.20
B	1.30+0.20/-0.15
C	1.30 MAX
D	0.45+0.15/-0.05
E	2.40+0.30/-0.20
G	1.90
H	0.95
J	0.13+0.10/-0.05
K	0.00 ~ 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/-0.10
P	7°

SOT-23

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	40	V
Reverse Voltage	V_R	40	V
Average Forward Current	I_O	0.5	A
Non-repetitive peak surge current	I_{FSM}	3	A
Junction Temperature	T_j	125	℃
Storage Temperature	T_{stg}	-55 ~ 125	℃

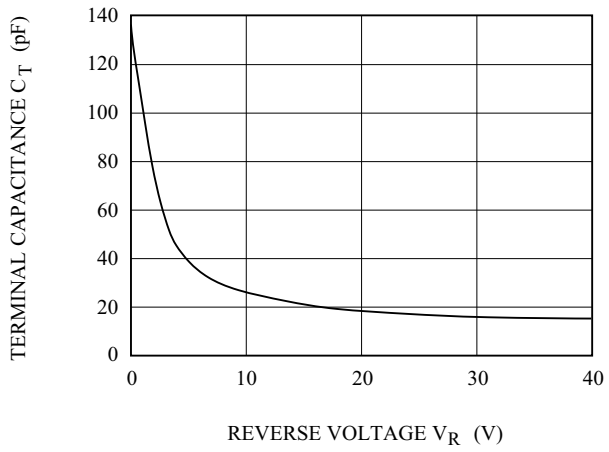
Marking



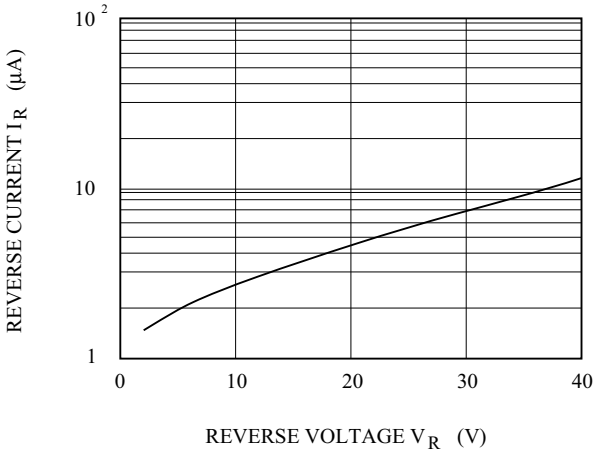
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	I_R=1mA	40	-	-	V
Forward Voltage	V_F	I_F=0.5A	-	0.45	0.55	V
Reverse Current	I_{R1}	V_R=10V	-	-	30	μA
	I_{R2}	V_R=25V	-	8	50	
Total Capacitance	C_{T1}	V_R=0V, f=1MHz	-	132	-	pF
	C_{T2}	V_R=10V, f=1MHz	-	25	-	

C_T - V_R



I_R - V_R



I_F - V_F